

# SPEC SHEET

## 2N5294



<b>Chip Appearance</b>	<b>Chip Size</b>	<b>1.9mm x 1.9mm</b>
	Chip Thickness	230 ± 20µm
	Bonding Pad Dimension	Base 665µm x 315µm
		Emitter 555 µm x 325 µm
	Scribe Line Width	50µm
	Top Metal	Al
	Back Metal	Ti-Ni-Ag
	Raper Size	4 inch

### Absolute Max Ratings (Ta=25°C)

(TO-220)

Item	Symbol	Max Ratings	Unit	Note
Collector-Base Voltage	V CBO	80	V	
Collector-Emitter Voltage	V CEO	70	V	
Emitter-Base Voltage	V EBO	7	V	
Collector Current	I C	4	mA	
Collector Loss (Power Dissipation)	P C	36	W	
Junction Temperature	T j		°C	
Storage Temperature	T stg	-65 to +150	°C	

### Electrical Characteristics (Ta=25°C)

(TO-220)

Item	Symbol	Min.	Typ.	Max.	Unit	Condition
Collector-Base Breakdown Voltage	BV CBO	80	-	-	V	I <sub>C</sub> = 100 µA
Collector-Emitter Breakdown Voltage	BV CEO	70	-	-	V	I <sub>C</sub> = 200 mA
Emitter-Base Breakdown Voltage	BV EBO	7	-	-	V	I <sub>E</sub> = 100 µA
Collector Cut-Off Current	I CBO	-	-	-	µA	V <sub>CB</sub> = V
Emitter Cut-Off Current	I EBO	-	-	1	mA	V <sub>EB</sub> = 7V
DC Current Gain	h FE	30	-	120	-	V <sub>CE</sub> = 4V, I <sub>C</sub> = 500mA
Collector Saturation	V CE(SAT)	-	-	1	V	I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA

### Probing Spec (Ta=25°C)

No.	Mode	Limit			Condition
		Min.	Max.	Unit	
1	V BE	-	-	V	I <sub>B</sub> =
2	BV CEO	70	-	V	I <sub>C</sub> = 200mA
3	I CBO	-	-	µA	V <sub>CB</sub> = V
4	I EBO	-	1	mA	V <sub>EB</sub> = 7V
5	I CEO	-	-	µA	V <sub>CE</sub> = V
6	h FE	30	120	-	V <sub>CE</sub> = 4V, I <sub>C</sub> = 500A
7	V CE(SAT)	-	1	V	I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA

